STABILIZED PHOTORESIST STRUCTURE FOR ETCHING PROCESS

ABSTRACT

A method for forming features in an etch layer is provided. A first mask is formed over the etch layer where the first mask defines a plurality of spaces with widths. The first mask is laterally etched where the etched first mask defines a plurality of spaces with widths that are greater than the widths of the spaces of the first mask. A sidewall layer is formed over the etched first mask where the sidewall layer defines a plurality of spaces with widths that are less than the widths of the spaces defined by the etched first mask. Features are etched into the etch layer through the sidewall layer, where the features have widths that are smaller than the widths of the spaces defined by the etched first mask. The mask and sidewall layer are removed.

Figure 1